

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of claims**

Claims 1-5. (canceled)

Claim 6. (previously presented) The method of claim 23, wherein:

said weight % of said nonaqueous solvent in said aqueous slurry/nonaqueous solvent mixture is increased until said aqueous slurry/nonaqueous solvent mixture is substantially free of said aqueous slurry.

Claim 7. (currently amended) The method of claim 25[[1]], wherein:

said nonaqueous solvent includes an ammine.

Claim 8. (currently amended) The method of claim 25[[1]], wherein:

said nonaqueous solvent includes dimethylsulfoxide.

Claim 9. (currently amended) The method of claim 25[[1]], wherein:

said nonaqueous solvent includes N,N-propanalamide.

Claim 10. (currently amended) The method of claim 25[[1]], wherein:

said nonaqueous solvent includes aniline.

Claim 11. (currently amended) The method of claim 25[[1]], wherein:

said nonaqueous solvent includes N,N-dimethylaniline.

Claim 12. (canceled)

Claim 13. (currently amended) ~~The method of claim 12,~~ A method of fabricating a semiconductor wafer, comprising:

\_\_\_\_\_ (a) subjecting a front side of said semiconductor wafer to chemical mechanical polishing using an aqueous slurry; and

\_\_\_\_\_ (b) disposing, a volume of nonaqueous liquid including a nonaqueous solvent onto said front side of said semiconductor wafer during said chemical mechanical polishing to rinse said semiconductor wafer,

\_\_\_\_\_ wherein:

said nonaqueous solvent includes an ammine.

Claims 14-20. (canceled)

Claim 21. (previously presented) A method of fabricating a semiconductor wafer, comprising:

(a) mixing an aqueous slurry containing an abrasive material and a nonaqueous solvent in a mixing unit so as to create a first volume of an aqueous slurry/nonaqueous solvent mixture with a first weight % of said nonaqueous solvent prior to being disposed onto said semiconductor wafer;

(b) disposing said first volume of the aqueous slurry/nonaqueous solvent mixture containing an abrasive material onto said a semiconductor wafer;

(c) polishing the semiconductor wafer with a polishing pad using said first volume;

(d) mixing said aqueous slurry containing an abrasive material and said nonaqueous solvent so as to create a second volume of an aqueous slurry/nonaqueous solvent mixture having a greater weight % of said nonaqueous solvent than said first weight % prior to being disposed onto said semiconductor wafer;

(e) disposing said second volume of said aqueous slurry/nonaqueous solvent mixture containing an abrasive material onto said semiconductor wafer;  
and

(f) polishing said semiconductor wafer using said second volume.

Claim 22. (previously presented) The method of claim 21, further comprising:

reducing the pressure of said polishing pad on said semiconductor wafer after disposing said first volume of said aqueous slurry/nonaqueous solvent mixture onto said semiconductor wafer and before completing disposing said second volume of said aqueous slurry/nonaqueous solvent mixture onto said semiconductor wafer.

Claim 23. (previously presented) The method of claim 21, wherein said disposing said second volume of aqueous slurry/nonaqueous solvent mixture further comprises:

disposing said second volume of aqueous slurry/nonaqueous solvent mixture during said polishing of said semiconductor wafer.

Claim 24. (previously presented) The method of claim 23, wherein mixing said second volume of an aqueous slurry/nonaqueous solvent mixture is performed at least partially simultaneously with disposing said first volume onto said semiconductor wafer, and mixing said second volume comprises:

controlling a flow of said nonaqueous solvent into said mixing unit.

Claim 25. (currently amended) ~~The method of claim 3, further comprising:~~ A method of fabricating a semiconductor wafer, comprising:

(a) disposing a volume of an aqueous slurry containing an abrasive material onto a semiconductor wafer and polishing the semiconductor wafer with a polishing pad, said polishing pad in contact with said semiconductor wafer when said volume of nonaqueous liquid is disposed onto said semiconductor wafer; and

(b) disposing a volume of nonaqueous liquid including a nonaqueous solvent onto said semiconductor wafer to rinse the semiconductor wafer.

(c) reducing the pressure of said polishing pad on said semiconductor wafer prior to completing disposing a volume of nonaqueous liquid including a nonaqueous solvent onto said semiconductor wafer.

Claim 26. (currently amended) The method of claim ~~[[12]]~~13, further comprising:

reducing the pressure of a polishing pad on said front side of said semiconductor wafer prior to completing disposing a volume of nonaqueous liquid including a nonaqueous solvent onto said front side of said semiconductor wafer.